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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION: GEUN-YOUNG YEOM, ET. AL.

FOR: METHOD OF ETCHING SEMICONDUCTOR DEVICE USING NEUTRAL  
BEAM AND APPARATUS FOR ETCHING THE SAME

AMENDMENT

The Assistant Commissioner of  
Patents and Trademarks  
Washington, DC 20231

Dear Sir:

"Express Mail" mailing label number EL914109912US  
Date of Deposit November 8, 2001  
I hereby certify that this paper or fee is being deposited  
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D.C. 20231.  
Jennifer Watson  
(Typed or printed name of person mailing paper or fee)  
[Signature]  
(Signature of person mailing paper or fee)

Before examining the present application, please preliminarily amend the  
specification, claims and abstract as follows:

IN THE CLAIMS

Please replace claims 1-13 with the following rewritten versions:

- A
- Sub B-7
1. (Amended) A method of etching a semiconductor device using a  
neutral beam comprising:  
extracting an ion beam having a predetermined polarity from an ion source to  
accelerate the ion beam;  
reflecting an accelerated ion beam by a reflector to neutralize the reflected ion  
beam; and  
positioning a substrate to be etched in a path of a neutral beam to etch a material  
layer on the substrate with the neutral beam.